

2SD1429

SILICON NPN TRIPLE DIFFUSED MESA TYPE

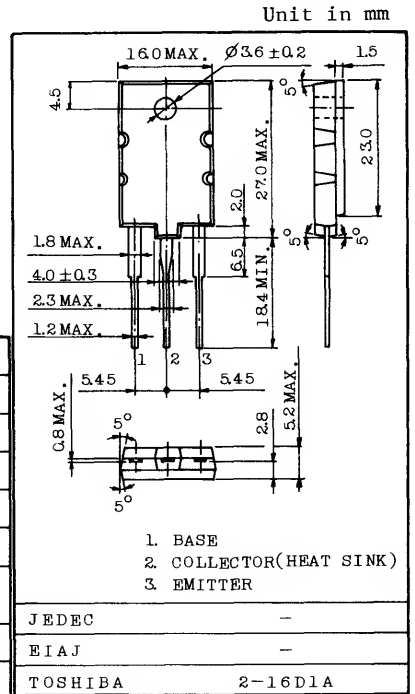
COLOR TV HORIZONTAL OUTPUT APPLICATIONS.

FEATURES:

- . High Voltage : $V_{CB0}=1500V$
- . Low Saturation Voltage : $V_{CE(sat)}=4V$ (Typ.)
- . High Speed : $t_f=0.5\mu s$ (Typ.)
- . Glass Passivated Collector-Base Junction

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	1500	V
Collector-Emitter Voltage	V_{CEO}	600	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	2.5	A
Emitter Current	I_E	-2.5	A
Collector Power Dissipation ($T_c=25^\circ C$)	P_C	80	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^\circ C$



Weight : 5.2g

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=500V, I_E=0$	-	-	10	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	1	mA
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=0.5A$	8	20	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2.0A, I_B=0.6A$	-	4	8	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=2.0A, I_B=0.6A$	-	-	1.5	V
Transition Frequency	f_T	$V_{CE}=10V, I_C=0.1A$	-	3	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	95	-	pF
Fall Time (Fig.)	t_f	$I_{CP}=2.0A, I_{B1}(end)=0.6A$	-	0.5	1.0	μs

Fig. t_f TEST CIRCUIT

